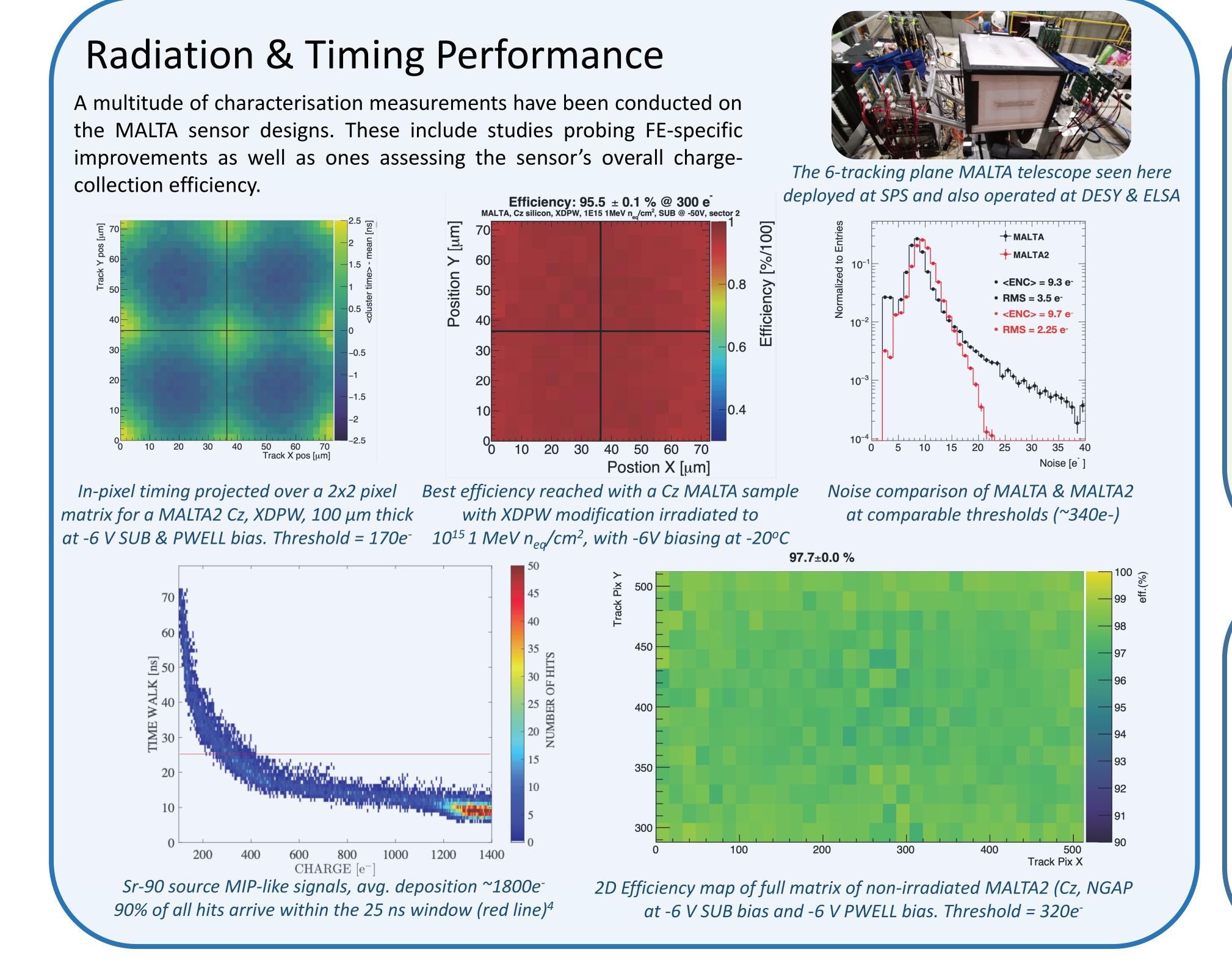
Radiation hardness and timing performance in MALTA monolithic Pixel sensors in Tower 180 nm

Abhishek Sharma (CERN) On behalf of the MALTA collaboration

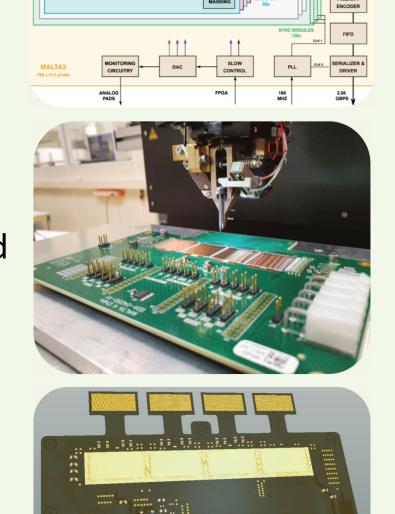
Motivation for Monolithic **Pixel Sensors** aluminum backside layer \odot high resistivity n-type silicon p-type silicon solder bump pixel readout electronic chip Hybrid Detector Design¹ **NWELL COLLECTION PMOS** ELECTRODE NWELL **NWELL PWELL PWELL** DEEP PWELL **DEEP PWELL** DEPLETED ZONE **DEPLETION** P- EPITAXIAL LAYER **BOUNDARY** P⁺ SUBSTRATE Monolithic Pixel Detector Design (ALPIDE²) + Large detector area + Reduced costs (no bump bonding) + Material reduction + High S/N ratio - Still under (radiation hardness) development

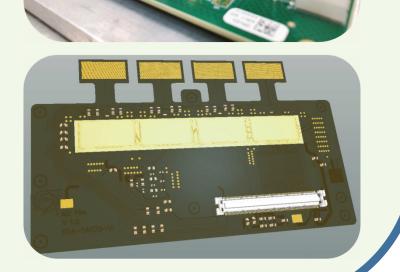
MALTA Sensor Development The first MALTA sensor was built as a full-scale demonstrator developed using The MALTA pixel 180 nm TowerJazz CMOS imaging technology. It comprised of 512 x 512 pixels analog/digital and is 21 x 20 mm² in size. Originally targeting application within the ATLAS Inner circuit tracker for the HL-LHC, this sensor has since undergone numerous iterations and branched out into different formfactors. ingle Chip Testboard MALTA1 Mini-MALTA MALTA C MALTA2 Jan 2018 Aug 2019 Jan 2019 Jan 2021 Full sized demonstrator Small demonstrator Asynchronous readout Improved slow control on New FE with additional Process and mask Variations in electrode size and **EPI & Cz substrates** process modifications modifications reset mechanisms **Suboptimal depletion** Full efficiency after **Enlarged cluster size and** Improved time resolution after irradiation $10^{15} \, n_{eq} / cm^2$ improved time resolution on Cz & slow control • The electric field strength in pixel corners can be significantly increased by process modifications. STD Czochralski samples allow for large depletion volumes LOW DOSE N-TYPE IMPLANT Standard pixel design with increasing substrate voltage, yielding large cluster with continuous low size as well as enhanced radiation tolerance. dose n-type implant ---- Modified process P- EPITAXIAL LAYER --- Additional p-implant ---- Gap in deep n-implant Fluence of 2e-08 10^{15} neq/cm² **NWELL COLLECTION PWELL** 1e-08 EXTRA DEEP PWELL LOW DOSE N-P- EPITAXIAL LAYER P- EPITAXIAL LAYER Time [s] TCAD simulation³ demonstrating the increased **XDPW** N-Gap charge collection time efficiency through the use Gap in the low dose Extra Deep P-Well of N-Gap and XDPW design modifications N-type implant



Next Steps & Parallel Developments

- MALTA3 full size sensor⁵ under design
- improved in-pixel digital electronics
- <1 ns time-stamping in periphery
- >1 Gb/s serial output communication
- **Chip-to-chip communication** assessments being conducted via dedicated 4-chip board using wire-bond connections with alternative interconnection techniques being
- Module formfactor design⁶ underway with very low material budget (50 um thick) flex PCB.





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investigated.

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⁴F. Piro et al., IEEE (2022), vol. 69, no. 6, pp. 1299-1309

⁵D. Dobrijević et al., NIMA (2022), 1040

pixel sensors" **TWEPP 2022**

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